

George Cirlin

List of Publications by Year in Descending Order

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The third column is the impact factor (IF) of the journal, and the fourth column is the number of citations of the article.

306
papers

4,211
citations

34
h-index

57
g-index

333
ext. papers

4,615
ext. citations

1.9
avg, IF

5.05
L-index

#	Paper	IF	Citations
306	III-V nanostructures with different dimensionality on silicon. <i>Journal of Physics: Conference Series</i> , 2021 , 2103, 012121	0.3	
305	Morphology transformation of InGaN nanowires grown on Si substrate by PA-MBE. <i>Journal of Physics: Conference Series</i> , 2021 , 2086, 012013	0.3	
304	Effect of the lattice mismatch on the efficiency of the GaAs nanowire/Si substrate solar cell. <i>Journal of Physics: Conference Series</i> , 2021 , 2015, 012004	0.3	0
303	III-V nanowires with quantum dots: MBE growth and properties. <i>Journal of Physics: Conference Series</i> , 2021 , 2015, 012124	0.3	
302	Influence of TOPO and TOPO-CdSe/ZnS Quantum Dots on Luminescence Photodynamics of InP/InAsP/InP Heterostructure Nanowires. <i>Nanomaterials</i> , 2021 , 11,	5.4	2
301	Selective-area growth and optical properties of GaN nanowires on patterned SiO _x /Si substrates. <i>Journal of Physics: Conference Series</i> , 2021 , 1851, 012006	0.3	
300	InP nanowires on Si(111) for piezotronic applications. <i>Journal of Physics: Conference Series</i> , 2021 , 1851, 012014	0.3	
299	Effect of crystal structure on the Young's modulus of GaP nanowires. <i>Nanotechnology</i> , 2021 , 32,	3.4	1
298	Formation of Hexagonal Ge Stripes on the Side Facets of AlGaAs Nanowires: Implications for Near-Infrared Detectors. <i>ACS Applied Nano Materials</i> , 2021 , 4, 7289-7294	5.6	1
297	Work function tailoring in gallium phosphide nanowires. <i>Applied Surface Science</i> , 2021 , 563, 150018	6.7	0
296	Directional Radiation from GaAs quantum dots in AlGaAs nanowires. <i>Technical Physics Letters</i> , 2021 , 47, 405-408	0.7	
295	III-V nanowires for ammonia detection. <i>Journal of Physics: Conference Series</i> , 2021 , 2086, 012186	0.3	
294	Separation of III-N partially-coalesced nanowire arrays from Si substrate. <i>Journal of Physics: Conference Series</i> , 2021 , 2086, 012191	0.3	
293	Features of the MBE growth of nanowires with quantum dots on the silicon surface. <i>Journal of Physics: Conference Series</i> , 2021 , 2086, 012032	0.3	
292	Complex Refractive of the Spectra Index of Mononucleotide Films on Silicon in the Terahertz Range. <i>Technical Physics Letters</i> , 2021 , 47, 862-864	0.7	
291	Structural and Optical Properties of Self-Catalyzed Axially Heterostructured GaPN/GaP Nanowires Embedded into a Flexible Silicone Membrane. <i>Nanomaterials</i> , 2020 , 10,	5.4	6
290	Nonlinear Bleaching of InAs Nanowires in the Visible Range. <i>Optics and Spectroscopy (English Translation of Optika I Spektroskopiya)</i> , 2020 , 128, 125-130	0.7	

289	Effect of the Uniaxial Compression on the GaAs Nanowire Solar Cell. <i>Micromachines</i> , 2020 , 11,	3.3	6
288	Deep-Subwavelength Raman Imaging of the Strained GaP Nanowires. <i>Journal of Physical Chemistry C</i> , 2020 , 124, 14054-14060	3.8	6
287	MBE-Grown In _x Ga _{1-x} As Nanowires with 50% Composition. <i>Semiconductors</i> , 2020 , 54, 650-653	0.7	1
286	MBE synthesis and properties of GaN NWs on SiC/Si substrate and InGaN nanostructures on Si substrate. <i>Journal of Physics: Conference Series</i> , 2020 , 1537, 012003	0.3	1
285	Hybrid AlGaAs nanowires on silicon: growth and properties. <i>Journal of Physics: Conference Series</i> , 2020 , 1537, 012002	0.3	
284	Peculiarities of the structural properties of In _x Ga _{1-x} N polytype nanostructures grown by molecular-beam epitaxy. <i>Journal of Physics: Conference Series</i> , 2020 , 1482, 012014	0.3	2
283	Hydrogen passivation of the n-GaN nanowire/p-Si heterointerface. <i>Nanotechnology</i> , 2020 , 31, 244003	3.4	5
282	The Role of Physical Models in the Description of Luminescence Kinetics of Hybrid Nanowires. <i>Optics and Spectroscopy (English Translation of Optika I Spektroskopiya)</i> , 2020 , 128, 119-124	0.7	5
281	Luminescence Photodynamics of Hybrid-Structured InP/InAsP/InP Nanowires Passivated by a Layer of TOPO-CdSe/ZnS Quantum Dots. <i>Semiconductors</i> , 2020 , 54, 1141-1146	0.7	4
280	Selective-Area Growth of GaN Nanowires on Patterned SiO _x /Si Substrates by Molecular Beam Epitaxy. <i>Technical Physics Letters</i> , 2020 , 46, 1080-1083	0.7	5
279	Specific Growth Features of Nanostructures for Terahertz Quantum Cascade Lasers and Their Physical Properties. <i>Semiconductors</i> , 2020 , 54, 1092-1095	0.7	2
278	Wet chemical etching of GaN or InGaN nanowires on Si substrate for micro and nano-devices fabrication. <i>Journal of Physics: Conference Series</i> , 2020 , 1695, 012047	0.3	
277	Multiply GaAs quantum dots in AlGaAs nanowires: MBE growth and properties. <i>Journal of Physics: Conference Series</i> , 2020 , 1695, 012205	0.3	
276	Optical properties of InGaN/GaN QDs nanorods by top-down fabrication after KOH treatment. <i>Journal of Physics: Conference Series</i> , 2020 , 1695, 012046	0.3	
275	Electrical properties of InGaN nanostructures with branched morphology synthesized via MBE on p-type Si(111). <i>Journal of Physics: Conference Series</i> , 2020 , 1695, 012030	0.3	
274	Modified silicone rubber for fabrication and contacting of flexible suspended membranes of n/p-GaP nanowires with a single-walled carbon nanotube transparent contact. <i>Journal of Materials Chemistry C</i> , 2020 , 8, 3764-3772	7.1	15
273	Fabrication and electrical study of large area free-standing membrane with embedded GaP NWs for flexible devices. <i>Nanotechnology</i> , 2020 , 31, 46LT01	3.4	6
272	Engineering of the Second-Harmonic Emission Directionality with III-V Semiconductor Rod Nanoantennas. <i>Laser and Photonics Reviews</i> , 2020 , 14, 2000028	8.3	9

271	Synthesis of Morphologically Developed InGaN Nanostructures on Silicon: Influence of the Substrate Temperature on the Morphological and Optical Properties. <i>Semiconductors</i> , 2020 , 54, 1075-1077	0.7	2
270	GaN nanowires/ p-Si interface passivation by hydrogen plasma treatment. <i>Journal of Physics: Conference Series</i> , 2020 , 1537, 012012	0.3	
269	Resonant excitation of nanowire quantum dots. <i>Npj Quantum Information</i> , 2020 , 6,	8.6	4
268	Ascending Si diffusion into growing GaN nanowires from the SiC/Si substrate: up to the solubility limit and beyond. <i>Nanotechnology</i> , 2020 , 31, 294003	3.4	3
267	InAs/InP core/shell nanowire gas sensor: Effects of InP shell on sensitivity and long-term stability. <i>Applied Surface Science</i> , 2019 , 498, 143756	6.7	4
266	The Influence of EL2 Centers on the Photoelectric Response of an Array of Radial GaAs/AlGaAs Nanowires. <i>Technical Physics Letters</i> , 2019 , 45, 835-838	0.7	
265	Nonradiative Energy Transfer in Hybrid Nanostructures with Varied Dimensionality. <i>Semiconductors</i> , 2019 , 53, 1258-1261	0.7	5
264	Control of Conductivity of InGaAs Nanowires by Applied Tension and Surface States. <i>Nano Letters</i> , 2019 , 19, 4463-4469	11.5	11
263	Surface state density in wurtzite InP nanowires. <i>Journal of Physics: Conference Series</i> , 2019 , 1199, 012021	0.3	
262	Effects of the surface preparation and buffer layer on the morphology, electronic and optical properties of the GaN nanowires on Si. <i>Nanotechnology</i> , 2019 , 30, 395602	3.4	22
261	InP/Si Heterostructure for High-Current Hybrid Triboelectric/Photovoltaic Generation. <i>ACS Applied Energy Materials</i> , 2019 , 2, 4395-4401	6.1	9
260	GaN-nanowire/Si solar cell: numerical modeling, fabrication and characterization. <i>Journal of Physics: Conference Series</i> , 2019 , 1199, 012030	0.3	0
259	Design and fabrication of terahertz quantum cascade laser with double metal waveguide based on multilayer GaAs/AlGaAs heterostructures. <i>IOP Conference Series: Materials Science and Engineering</i> , 2019 , 475, 012020	0.4	1
258	Growth and Characterization of GaP/GaPAs Nanowire Heterostructures with Controllable Composition. <i>Physica Status Solidi - Rapid Research Letters</i> , 2019 , 13, 1900350	2.5	19
257	A new insight into the mechanism of low-temperature Au-assisted growth of InAs nanowires. <i>CrystEngComm</i> , 2019 , 21, 4707-4717	3.3	5
256	Triboelectric current generation in InP. <i>Journal of Physics: Conference Series</i> , 2019 , 1400, 066055	0.3	1
255	InGaN nanostructures of a branched morphology on silicon substrate: MBE synthesis and properties. <i>Journal of Physics: Conference Series</i> , 2019 , 1410, 012052	0.3	
254	Photovoltaic properties of InP NWs/p-Si heterostructure. <i>Journal of Physics: Conference Series</i> , 2019 , 1410, 012060	0.3	

253	Structural and Optical Properties of GaAs Nanowires Grown by MBE on Si(111) Substrate. <i>Journal of Physics: Conference Series</i> , 2019 , 1410, 012062	0.3	
252	Synthesis by Molecular Beam Epitaxy and Properties of InGaN Nanostructures of Branched Morphology on a Silicon Substrate. <i>Technical Physics Letters</i> , 2019 , 45, 1111-1113	0.7	4
251	InGaN/GaN QDs nanorods for light emitters: Processing and properties 2019 ,		1
250	Ultrafast Dynamics of Photoinduced Electron-Hole Plasma in Semiconductor Nanowires. <i>Semiconductors</i> , 2018 , 52, 19-23	0.7	
249	Fine Structure of Levels and Piezospectroscopy of A+ Centers in GaAs/AlGaAs Quantum Wells. <i>Physics of the Solid State</i> , 2018 , 60, 339-346	0.8	0
248	MBE growth and Structural Properties of InAs and InGaAs Nanowires with Different Mole Fraction of In on Si and Strongly Mismatched SiC/Si(111) Substrates. <i>Semiconductors</i> , 2018 , 52, 651-653	0.7	2
247	GaAs Wurtzite Nanowires for Hybrid Piezoelectric Solar Cells. <i>Semiconductors</i> , 2018 , 52, 609-611	0.7	6
246	Optical Properties of GaN Nanowires Grown by MBE on SiC/Si(111) Hybrid Substrate. <i>Semiconductors</i> , 2018 , 52, 602-604	0.7	
245	The Features of GaAs Nanowire SEM Images. <i>Semiconductors</i> , 2018 , 52, 605-608	0.7	
244	Coherent Growth of InP/InAsP/InP Nanowires on a Si (111) Surface by Molecular-Beam Epitaxy. <i>Technical Physics Letters</i> , 2018 , 44, 112-114	0.7	9
243	GaP/Si(111) Nanowire Crystals Synthesized by Molecular-Beam Epitaxy with Switching between the Hexagonal and Cubic Phases. <i>Semiconductors</i> , 2018 , 52, 1-5	0.7	1
242	Hybrid GaAs/AlGaAs Nanowire-Quantum dot System for Single Photon Sources. <i>Semiconductors</i> , 2018 , 52, 462-464	0.7	9
241	MBE growth of thin AlGaAs nanowires with a complex structure on strongly mismatched SiC/Si(111) substrate. <i>Journal of Physics: Conference Series</i> , 2018 , 1038, 012063	0.3	1
240	Dopant-stimulated growth of GaN nanotube-like nanostructures on Si(111) by molecular beam epitaxy. <i>Beilstein Journal of Nanotechnology</i> , 2018 , 9, 146-154	3	25
239	Droplet epitaxy mediated growth of GaN nanostructures on Si (111) via plasma-assisted molecular beam epitaxy. <i>CrystEngComm</i> , 2018 , 20, 3370-3380	3.3	23
238	Core-Shell III-Nitride Nanowire Heterostructure: Negative Differential Resistance and Device Application Potential. <i>Semiconductors</i> , 2018 , 52, 489-492	0.7	3
237	The generation of an optimised SiGe superlattice: growth, structure and optical properties 2018 , 255-258		
236	Piezoelectric Current Generation in Wurtzite GaAs Nanowires. <i>Physica Status Solidi - Rapid Research Letters</i> , 2018 , 12, 1700358	2.5	10

235	New method for MBE growth of GaAs nanowires on silicon using colloidal Au nanoparticles. <i>Nanotechnology</i> , 2018 , 29, 045602	3.4	5
234	MBE growth and properties of GaAs, AlGaAs and InAs nanowires on SiC/Si(111) hybrid substrate. <i>Journal of Physics: Conference Series</i> , 2018 , 1135, 012036	0.3	
233	Self-Catalyzed MBE-Grown GaP Nanowires on Si(111): V/III Ratio Effects on the Morphology and Crystal Phase Switching. <i>Semiconductors</i> , 2018 , 52, 2092-2095	0.7	11
232	Microlens-Enhanced Substrate Patterning and MBE Growth of GaP Nanowires. <i>Semiconductors</i> , 2018 , 52, 2088-2091	0.7	14
231	Structural and Optical Properties of Wurtzite AlGaAs Nanowires Grown by MBE on Si(111) Substrate. <i>Semiconductors</i> , 2018 , 52, 2146-2148	0.7	2
230	Structural properties of multilayer heterostructure for quantum-cascade lasers grown by MBE growth. <i>Journal of Physics: Conference Series</i> , 2018 , 1124, 022005	0.3	
229	Electrical Properties of GaAs Nanowires Grown on Graphene/SiC Hybrid Substrates. <i>Semiconductors</i> , 2018 , 52, 1611-1615	0.7	2
228	Solar Cell Based on Core/Shell Nanowires. <i>Semiconductors</i> , 2018 , 52, 1568-1572	0.7	3
227	MBE growth of GaAs nanowires with modulated crystal structure. <i>Journal of Physics: Conference Series</i> , 2018 , 1124, 022043	0.3	
226	Electromechanical Switch Based on In _x Ga _{1-x} As Nanowires. <i>Semiconductors</i> , 2018 , 52, 1833-1835	0.7	4
225	Effect of the Conductive Channel Cut-Off on Operation of n ⁺ GaN NW-Based Gunn Diode. <i>Semiconductors</i> , 2018 , 52, 1809-1812	0.7	
224	MBE Growth and Structural Properties of GaP and InP Nanowires on a SiC Substrate with a Graphene Layer. <i>Semiconductors</i> , 2018 , 52, 1428-1431	0.7	2
223	Phosphorus-Based Nanowires Grown by Molecular-Beam Epitaxy on Silicon. <i>Semiconductors</i> , 2018 , 52, 1416-1419	0.7	2
222	Nanowire Quantum Dots Tuned to Atomic Resonances. <i>Nano Letters</i> , 2018 , 18, 7217-7221	11.5	21
221	Anapoles in Free-Standing III-V Nanodisks Enhancing Second-Harmonic Generation. <i>Nano Letters</i> , 2018 , 18, 3695-3702	11.5	75
220	Unified mechanism of the surface Fermi level pinning in III-As nanowires. <i>Nanotechnology</i> , 2018 , 29, 314003	0.3	17
219	MBE Growth and Optical Properties of GaN, InN, and A ₃ B ₅ Nanowires on SiC/Si(111) Hybrid Substrate. <i>Advances in Condensed Matter Physics</i> , 2018 , 2018, 1-5	1	
218	Energy spectrum and thermal properties of a terahertz quantum-cascade laser based on the resonant-phonon depopulation scheme. <i>Semiconductors</i> , 2017 , 51, 514-519	0.7	11

217	Terahertz radiation generation in multilayer quantum-cascade heterostructures. <i>Technical Physics Letters</i> , 2017 , 43, 362-365	0.7	18
216	AlGaAs and AlGaAs/GaAs/AlGaAs nanowires grown by molecular beam epitaxy on silicon substrates. <i>Journal Physics D: Applied Physics</i> , 2017 , 50, 484003	3	15
215	Directional emission from beryllium doped GaAs/AlGaAs nanowires. <i>Technical Physics Letters</i> , 2017 , 43, 811-813	0.7	2
214	MBE growth of nanowires using colloidal Ag nanoparticles. <i>Journal of Physics: Conference Series</i> , 2017 , 864, 012010	0.3	2
213	Modeling the semiconductor devices with negative differential resistance based on nitride nanowires. <i>Journal of Physics: Conference Series</i> , 2017 , 917, 082017	0.3	2
212	The dependence of the wavelength on MBE growth parameters of GaAs quantum dot in AlGaAs NWs on Si (111) substrate. <i>Journal of Physics: Conference Series</i> , 2017 , 929, 012047	0.3	2
211	MBE growth of ultrathin III ν nanowires on a highly mismatched SiC/Si(111) substrate. <i>Semiconductors</i> , 2017 , 51, 1472-1476	0.7	1
210	MBE growth and optical properties of GaN layers on SiC/Si(111) hybrid substrate. <i>Journal of Physics: Conference Series</i> , 2017 , 917, 032014	0.3	
209	MBE synthesis of (In,Mn)As quantum dots using Mn selective doping. <i>Journal of Crystal Growth</i> , 2017 , 468, 680-682	1.6	1
208	Researching the electrical properties of single A3B5 nanowires. <i>Journal of Physics: Conference Series</i> , 2017 , 917, 032042	0.3	1
207	MBE growth of GaAs and InAs nanowires using colloidal Ag nanoparticles. <i>Journal of Physics: Conference Series</i> , 2017 , 917, 032035	0.3	1
206	Thermal Penetration of Gold Nanoparticles into Silicon Dioxide. <i>Acta Physica Polonica A</i> , 2017 , 132, 366-369		9
205	MBE growth, structural and optical properties of multilayer heterostructures for quantum-cascade lasers. <i>Journal of Physics: Conference Series</i> , 2017 , 917, 052012	0.3	2
204	Numerical simulation of the properties of solar cells based on GaPNAs/Si heterostructures and GaN nanowires. <i>Semiconductors</i> , 2016 , 50, 1521-1525	0.7	8
203	Hybrid AlGaAs/GaAs/AlGaAs nanowires with a quantum dot grown by molecular beam epitaxy on silicon. <i>Semiconductors</i> , 2016 , 50, 1421-1424	0.7	15
202	Piezoelectric effect in wurtzite GaAs nanowires: Growth, characterization, and electromechanical 3D modeling. <i>Physica Status Solidi (A) Applications and Materials Science</i> , 2016 , 213, 3014-3019	1.6	8
201	Origin of Spontaneous Core/Shell AlGaAs Nanowires Grown by Molecular Beam Epitaxy. <i>Crystal Growth and Design</i> , 2016 , 16, 7251-7255	3.5	27
200	Growth and optical properties of filamentary GaN nanocrystals grown on a hybrid SiC/Si(111) substrate by molecular beam epitaxy. <i>Physics of the Solid State</i> , 2016 , 58, 1952-1955	0.8	10

199	Fabrication of a terahertz quantum-cascade laser with a double metal waveguide based on multilayer GaAs/AlGaAs heterostructures. <i>Semiconductors</i> , 2016 , 50, 1377-1382	0.7	13
198	MBE growth and optical properties of GaN nanowires on SiC/Si(111) hybrid substrate 2016 ,		6
197	Simulation of photovoltaic efficiency of a tandem solar cell on Si with GaN nanowires as an emitter layer. <i>Journal of Physics: Conference Series</i> , 2016 , 690, 012041	0.3	3
196	Electron beam induced current microscopy investigation of GaN nanowire arrays grown on Si substrates. <i>Materials Science in Semiconductor Processing</i> , 2016 , 55, 72-78	4.3	8
195	Growth and properties of self-catalyzed (In,Mn)As nanowires. <i>Physica Status Solidi - Rapid Research Letters</i> , 2016 , 10, 554-557	2.5	3
194	Piezoelectric effect in GaAs nanowires: experiment and theory. <i>Physica Status Solidi - Rapid Research Letters</i> , 2016 , 10, 172-175	2.5	8
193	Fabrication of the structures with autocatalytic CdTe nanowires using magnetron sputtering deposition. <i>Physics of the Solid State</i> , 2016 , 58, 2401-2405	0.8	2
192	Mn-assisted molecular-beam epitaxy growth (Ga,Mn)As nanowires. <i>Journal of Physics: Conference Series</i> , 2016 , 769, 012077	0.3	
191	The use of SiC/Si(111) hybrid substrate for MBE growth of GaN nanowires. <i>Journal of Physics: Conference Series</i> , 2016 , 741, 012027	0.3	3
190	Study of electrical properties of single GaN nanowires grown by molecular beam epitaxy. <i>Journal of Physics: Conference Series</i> , 2016 , 741, 012002	0.3	0
189	Surface passivation of GaAs nanowires by the atomic layer deposition of AlN. <i>Semiconductors</i> , 2016 , 50, 1619-1621	0.7	0
188	Synthesis of GaN nanowires on Si (111) substrates by molecular beam epitaxy. <i>Journal of Physics: Conference Series</i> , 2016 , 741, 012044	0.3	
187	Electronic structure of (In,Mn)As quantum dots buried in GaAs investigated by soft-x-ray ARPES. <i>Nanotechnology</i> , 2016 , 27, 425706	3.4	3
186	Terahertz Quantum-Cascade Laser Based on the Resonant-Phonon Depopulation Scheme. <i>International Journal of High Speed Electronics and Systems</i> , 2016 , 25, 1640022	0.5	5
185	Polarization of the photoluminescence of quantum dots incorporated into quantum wires. <i>Semiconductors</i> , 2016 , 50, 1647-1650	0.7	
184	Resonant features of the terahertz generation in semiconductor nanowires. <i>Semiconductors</i> , 2016 , 50, 1561-1565	0.7	2
183	Investigation of non-equilibrium electron-hole plasma in nanowires by THz spectroscopy. <i>Optics and Spectroscopy (English Translation of Optika I Spektroskopiya)</i> , 2016 , 120, 751-755	0.7	
182	Multilayer heterostructures for quantum-cascade lasers operating in the terahertz frequency range. <i>Semiconductors</i> , 2016 , 50, 662-666	0.7	7

181	Inorganic photovoltaics [Planar and nanostructured devices. <i>Progress in Materials Science</i> , 2016 , 82, 294-404	42.2	38
180	Polar Second-Harmonic Imaging to Resolve Pure and Mixed Crystal Phases along GaAs Nanowires. <i>Nano Letters</i> , 2016 , 16, 6290-6297	11.5	36
179	Photoelectric properties of an array of axial GaAs/AlGaAs nanowires. <i>Technical Physics Letters</i> , 2015 , 41, 443-447	0.7	6
178	Optical limiting in solutions of InP and GaAs nanowires and hybrid systems based on such nanocrystals. <i>Technical Physics Letters</i> , 2015 , 41, 120-123	0.7	3
177	Ex post manipulation of barriers in InGaAs tunnel injection devices. <i>Applied Physics Letters</i> , 2015 , 106, 013104	3.4	2
176	Modeling, synthesis and study of highly efficient solar cells based on III-nitride nanowire arrays grown on Si substrates. <i>Journal of Physics: Conference Series</i> , 2015 , 643, 012115	0.3	10
175	Generation of terahertz radiation by AlGaAs nanowires. <i>JETP Letters</i> , 2015 , 102, 316-320	1.2	2
174	Temperature quenching of spontaneous emission in tunnel-injection nanostructures. <i>Semiconductors</i> , 2015 , 49, 1483-1492	0.7	1
173	Generation of terahertz radiation in ordered arrays of GaAs nanowires. <i>Applied Physics Letters</i> , 2015 , 106, 252104	3.4	15
172	MBE growth and optical properties of GaAs nanowires grown on Si(111) substrate using two-temperature steps regime. <i>Journal of Physics: Conference Series</i> , 2015 , 643, 012003	0.3	
171	Numerical modeling of photovoltaic efficiency of n-type GaN nanowires on p-type Si heterojunction. <i>Physica Status Solidi - Rapid Research Letters</i> , 2015 , 9, 507-510	2.5	23
170	Development of methods for orderly growth of nanowires. <i>Journal of Physics: Conference Series</i> , 2015 , 661, 012053	0.3	0
169	The Effect of External Gaseous Environments on the Photoluminescence Intensity of Quantum-Dimensional Composite System. <i>Journal of Nanomaterials</i> , 2015 , 2015, 1-4	3.2	2
168	Electrical detection of picosecond acoustic pulses in vertical transport devices with nanowires. <i>Applied Physics Letters</i> , 2014 , 104, 062102	3.4	2
167	Effect of nanobridges on the emission spectra of a quantum dot-quantum well tunneling pair. <i>Semiconductors</i> , 2014 , 48, 1178-1184	0.7	2
166	Nanospectroscopic Imaging of Twinning Superlattices in an Individual GaAs-AlGaAs Core/Shell Nanowire. <i>ACS Photonics</i> , 2014 , 1, 1099-1106	6.3	14
165	Study of the electrical properties of individual (Ga,Mn)As nanowires. <i>Semiconductors</i> , 2014 , 48, 344-349	0.7	2
164	(In,Mn)As multilayer quantum dot structures. <i>Applied Physics Letters</i> , 2014 , 105, 232101	3.4	3

163	Novel TEM sample preparation using XeF ₂ selective Etching. <i>Materials Research Society Symposia Proceedings</i> , 2014 , 1659, 149-153		
162	Ultrafast carrier dynamics in GaAs nanowires. <i>Lithuanian Journal of Physics</i> , 2014 , 54, 41-45	1.1	1
161	Formation of structures with noncatalytic CdTe nanowires. <i>Semiconductors</i> , 2013 , 47, 875-878	0.7	3
160	Terahertz generation by GaAs nanowires. <i>Applied Physics Letters</i> , 2013 , 103, 072108	3.4	25
159	Computer simulation of the structure and raman spectra of GaAs polytypes. <i>Physics of the Solid State</i> , 2013 , 55, 1220-1230	0.8	3
158	Photovoltaic properties of GaAs:Be nanowire arrays. <i>Semiconductors</i> , 2013 , 47, 808-811	0.7	3
157	Optical anisotropy of InGaAs quantum dots. <i>Semiconductors</i> , 2013 , 47, 85-89	0.7	1
156	Ultra-low density InAs quantum dots. <i>Semiconductors</i> , 2013 , 47, 1324-1327	0.7	1
155	New method of determining the young's Modulus of (Ga,Mn)As nanowhiskers with a scanning electron microscope. <i>Physics of the Solid State</i> , 2013 , 55, 2229-2233	0.8	1
154	Effect of an arsenic flux on the molecular-beam epitaxy of self-catalytic (Ga,Mn)As nanowire crystals. <i>Semiconductors</i> , 2013 , 47, 1416-1421	0.7	2
153	Growth specifics of GaAs nanowires in mesa. <i>Physics of the Solid State</i> , 2013 , 55, 702-706	0.8	
152	(In,Mn)As quantum dots: Molecular-beam epitaxy and optical properties. <i>Semiconductors</i> , 2013 , 47, 1037-1040	1.0	6
151	Model of a GaAs Quantum Dot Embedded in a Polymorph AlGaAs Nanowire. <i>IEEE Journal of Selected Topics in Quantum Electronics</i> , 2013 , 19, 1-9	3.8	10
150	Composite system based on CdSe/ZnS quantum dots and GaAs nanowires. <i>Semiconductors</i> , 2013 , 47, 1346-1350	0.7	10
149	Ferromagnetic (Ga,Mn)As nanowires grown by Mn-assisted molecular beam epitaxy. <i>Journal of Applied Physics</i> , 2013 , 113, 144303	2.5	12
148	Formation of (Ga,Mn)As nanowires and study of their magnetic properties. <i>Semiconductors</i> , 2012 , 46, 179-183	0.7	11
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